Central Semiconductor
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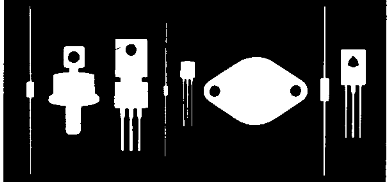

SE9303 SE9304 SE9305 NPN
SE9403 SE9404 SE9405 PNP

SILICON POWER DARLINGTON COMPLEMENTARY TRANSISTORS

JEDEC TO-3 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR SE9303, SE9403 Series Types are Complementary Silicon Power Darlington Transistors designed for audio amplifier and power linear and switching applications.

MAXIMUM RATINGS ($T_C=25^\circ C$)

	SYMBOL	SE9303 SE9403	SE9304 SE9404	SE9305 SE9405	UNIT
Collector-Base Voltage	V_{CBO}	60	80	100	V
Collector-Emitter Voltage	V_{CEO}	60	80	100	V
Emitter-Base Voltage	V_{EBO}	5.0	5.0	5.0	V
Collector Current	I_C	10	10	10	A
Power Dissipation	P_D	100	100	100	W
Operating and Storage Junction Temperature	T_J, T_{stg}		-65 TO +200		°C

ELECTRICAL CHARACTERISTICS ($T_C=25^\circ C$)

		SE9303 SE9403		SE9304 SE9404		SE9305 SE9405		
SYMBOL	TEST CONDITIONS	MIN	MAX	MIN	MAX	MIN	MAX	UNIT
I_{CBO}	V_{CE}=Rated V_{CEO}		200		200		200	µA
I_{CEO}	$V_{CE}=\frac{1}{2}$ Rated V_{CEO}		500		500		500	µA
I_{EBO}	V_{EB}=5.0V		4.0		4.0		4.0	mA
BV_{CEO}	I_C=100mA	60		80		100		V
$V_{CE(SAT)}$	I_C=4.0A, I_B=16mA		2.0		2.0		2.0	V
$V_{CE(SAT)}$	I_C=7.5A, I_B=150mA		2.5		2.5		2.5	V
$V_{BE(ON)}$	V_{CE}=3.0V, I_C=4.0A		2.5		2.5		2.5	V
$V_{BE(ON)}$	V_{CE}=3.0V, I_C=7.5A		3.0		3.0		3.0	V
h_{FE}	V_{CE}=3.0V, I_C=1.0A	750		750		750		-
h_{FE}	V_{CE}=3.0V, I_C=4.0A	1000		1000		1000		-
h_{FE}	V_{CE}=3.0V, I_C=7.5A	100		100		100		-
f_T	V_{CE}=3.0V, I_C=4.0A, f=1.0MHz	1.0		1.0		1.0		MHz